

## **FJA3835**

### **Power Amplifier**

- High Current Capability : I<sub>C</sub>=8A
- High Power Dissipation
- Wide S.O.A



## **NPN Epitaxial Silicon Transistor**

## Absolute Maximum Ratings $T_C=25^{\circ}C$ unless otherwise noted

| Symbol           | Parameter                                    | Value      | Units |
|------------------|--|------------|-------|
| V <sub>CBO</sub> | Collector-Base Voltage                       | 200        | V     |
| V <sub>CEO</sub> | Collector-Emitter Voltage                    | 120        | V     |
| V <sub>EBO</sub> | Emitter-Base Voltage                         | 8          | V     |
| I <sub>C</sub>   | Collector Current (DC)                       | 8          | Α     |
| I <sub>CP</sub>  | Collector Current (Pulse)                    | 16         | Α     |
| PC               | Collector Dissipation (T <sub>C</sub> =25°C) | 80         | W     |
| TJ               | Junction Temperature                         | 150        | °C    |
| T <sub>STG</sub> | Storage Temperature                          | - 55 ~ 150 | °C    |

## Electrical Characteristics $T_C=25$ °C unless otherwise noted

| Symbol                | Parameter                            | Test Condition   | Min. | Тур. | Max. | Units |
|-----------------------|--------------------------------------|--|------|------|------|-------|
| BV <sub>CBO</sub>     | Collector-Base Breakdown Voltage     | $I_C=5mA$ , $I_E=0$                                      | 200  |      |      | V     |
| BV <sub>CEO</sub>     | Collector-Emitter Breakdown Voltage  | I <sub>C</sub> =10mA, R <sub>BE</sub> =∞                 | 120  |      |      | V     |
| BV <sub>EBO</sub>     | Emitter-Base Breakdown Voltage       | $I_E=5mA$ , $I_C=0$                                      | 8    |      |      | V     |
| I <sub>CBO</sub>      | Collector Cut-off Current            | $V_{CB}$ =80V, $I_{E}$ =0                                |      |      | 0.1  | mA    |
| I <sub>EBO</sub>      | Emitter Cut-off Current              | $V_{EB}$ =4V, $I_{C}$ =0                                 |      |      | 0.1  | mA    |
| h <sub>FE</sub>       | * DC Current Gain                    | $V_{CE}$ =4V, $I_{C}$ =3A                                | 120  |      | 250  |       |
| V <sub>CE</sub> (sat) | Collector-Emitter Saturation Voltage | I <sub>C</sub> =3A, I <sub>B</sub> =0.3A                 |      |      | 0.5  | V     |
| V <sub>BE</sub> (sat) | Base-Emitter On Voltage              | I <sub>C</sub> =3A, I <sub>B</sub> =0.3A                 |      |      | 1.2  | V     |
| f <sub>T</sub>        | Current Gain Bandwidth Product       | V <sub>CE</sub> =5V, I <sub>C</sub> =1A                  |      | 30   |      | MHz   |
| C <sub>ob</sub>       | Output Capacitance                   | V <sub>CB</sub> =10V, f=1MHz                             |      | 210  |      | pF    |
| t <sub>ON</sub>       | Turn On Time                         | V <sub>CC</sub> =20V,                                    |      | 0.26 |      | μs    |
| t <sub>F</sub>        | Fall Time                            | I <sub>C</sub> =1A=10I <sub>B1</sub> =-10I <sub>B2</sub> |      | 0.68 |      | μs    |
| t <sub>STG</sub>      | Storage Time                         | $R_L=20\Omega$   |      | 6.68 |      | μs    |

\* Pulse Test : PW=20µs

## **Typical Characteristics**

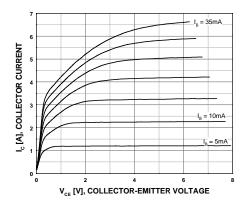


Figure 1. Static Characterstic

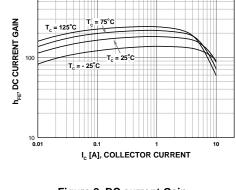


Figure 2. DC current Gain

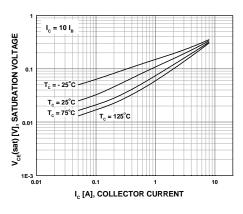


Figure 3. Collector-Emitter Saturation Voltage

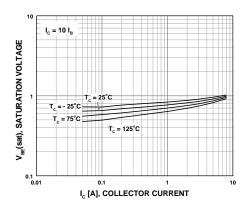


Figure 4. Base-Emitter Saturation Voltage

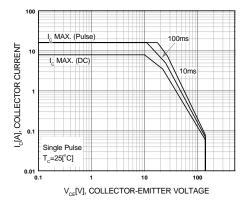


Figure 5. Safe Operating Area

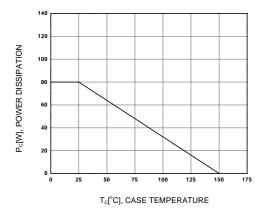
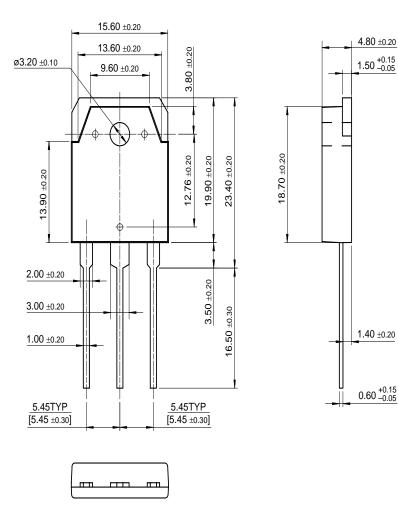


Figure 6. Power Derating

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# **Package Demensions**

# TO-3P



Dimensions in Millimeters

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